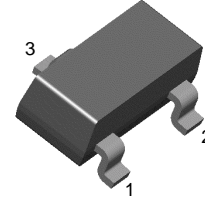


**General Purpose Transistor**



SOT-323

1. Base 2. Emitter 3. Collector

**PNP Epitaxial TY Transistor**

**Absolute Maximum Ratings**  $T_a=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CES}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-600	mA
$P_C$	Collector Power Dissipation	325	mW
$T_{STG}$	Storage Temperature	150	$^{\circ}\text{C}$

**Electrical Characteristics**  $T_a=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60		V
$BV_{CEO}$	* Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}, I_B = 0$	-60		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -50\text{V}, I_E = 0$		-0.01	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = -10\text{V}, I_E = -0.1\text{mA}$ $V_{CE} = -10\text{V}, I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -150\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -500\text{mA}$	75 100 100 100 50	300	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.4 -1.6	V V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.3 -2.6	V V
$f_T$	Current Gain Bandwidth Product	$I_C = -50\text{mA}, V_{CE} = -20\text{V}, f = 100\text{MHz}$	200		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		8	pF
$t_{ON}$	Turn On Time	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$		45	ns
$t_{OFF}$	Turn Off Time	$V_{CC} = -6\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = 15\text{mA}$		100	ns

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

Marking

